

L Number	Hits	Search Text	DB	Time stamp
-	226	semiconduct\$3 and HMDS with prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/19 18:13
-	2005	semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:26
-	10	((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 19:47
-	6246	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:03
-	1152	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:21
-	12	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) and ((develop\$4 or rins\$3) or spin\$4 or rotat\$3 or turn\$3 or speed\$3) same (exhaust\$3 or air) near\$ (velocity\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:10
-	130	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near\$ (velocity\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:23
-	11	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near\$ (velocity\$3 or speed\$3) and (develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near\$ (velocity\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:24
-	1347	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:21

-	179	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:22
-	11	((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$3 or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:06
-	1091	((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$3 or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:12
-	825	((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$3 or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) ) and (semiconduct\$3 or wafer or silicon or "Si")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:15

-	320	(((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:18
-	39	(((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7: same (prim\$3 or pre adj treat\$3 or pretreat\$3) ("4556785").PN.	USPAT; US-PGFUB; EPO; JPO; IBM_TDB	2003/06/23 16:44
-	1		USPAT; US-PGFUB	2003/06/21 16:17
-	443	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)	USPAT; US-PGFUB; EPO; JPO; IBM_TDB	2003/06/21 19:53
-	237	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and ((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) same (seconds or "sec"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:06

-	85	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:08
-	6097	((resist or photoresist or photopolymer\$7) same (develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:57

-	721	430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3) not (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:56
-	141	430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same (develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3) not (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/24 11:47